# **BLP05H6110XR**

# **Power LDMOS transistor**

Rev. 1 — 18 May 2015

**Objective data sheet** 

## 1. Product profile

### 1.1 General description

A 110 W extremely rugged LDMOS power transistor for broadcast and industrial applications in the HF to 600 MHz band.

Table 1. Application information

Test signal	f	V <sub>DS</sub>	PL	G <sub>p</sub>	$\eta_D$
	(MHz)	(V)	(W)	(dB)	(%)
pulsed RF	108	50	110	27	75

#### 1.2 Features and benefits

- Easy power control
- Integrated ESD protection
- Excellent ruggedness
- High efficiency
- Excellent thermal stability
- Designed for broadband operation (HF to 600 MHz)
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

## 1.3 Applications

- Industrial, scientific and medical applications
- Broadcast transmitter applications



## 2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	gate 2		,
2	gate 1	4 3	4
3	drain 1		
4	drain 2	pin 1 index	5
5	source	[1]	2
			3 aaa-003574

[1] Connected to flange.

## 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BLP05H6110XR	HSOP4F	plastic, heatsink small outline package; 4 leads(flat)	SOT1223-2

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage		-	135	V
$V_{GS}$	gate-source voltage		-6	+11	V
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature	[1	l -	225	°C

<sup>[1]</sup> Continuous use at maximum temperature will affect the reliability, for details refer to the on-line MTF

## 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions		Тур	Unit
R <sub>th(j-c)</sub>	thermal resistance from junction to case	T <sub>j</sub> = 150 °C	[1][2]	<tbd></tbd>	K/W
Z <sub>th(j-c)</sub>	transient thermal impedance from junction to case	$T_j$ = 150 °C; $t_p$ = 100 $\mu$ s; $\delta$ = 20 %	[3]	<tbd></tbd>	K/W

- [1]  $T_i$  is the junction temperature.
- [2]  $R_{th(j-c)}$  is measured under RF conditions.
- [3] See <tbd>.

BLP05H6110XR

### 6. Characteristics

#### Table 6. DC characteristics

 $T_i = 25$  °C; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 0.375 \text{ mA}$	135	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$V_{DS} = 10 \text{ V}; I_D = 37.5 \text{ mA}$	1.25	1.8	2.25	V
$V_{GSq}$	gate-source quiescent voltage	$V_{DS} = 50 \text{ V}; I_D = 10 \text{ mA}$	-	1.7	-	V
I <sub>DSS</sub>	drain leakage current	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 50 V	-	-	1.4	μΑ
I <sub>DSX</sub>	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	5.4	-	A
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 11 V; V <sub>DS</sub> = 0 V	-	-	140	nA
R <sub>DS(on)</sub>	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 1.31 \text{ A}$	-	1.1	-	Ω

#### Table 7. AC characteristics

 $T_i$  = 25 °C; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C <sub>rs</sub>	feedback capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}; f = 1 \text{ MHz}$	-	0.4	-	pF
C <sub>iss</sub>	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}; f = 1 \text{ MHz}$	-	46	-	pF
C <sub>oss</sub>	output capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}; f = 1 \text{ MHz}$	-	17	-	pF

#### Table 8. RF characteristics

Test signal: pulsed RF;  $t_p$  = 100  $\mu$ s;  $\delta$  = 20 %; f = 108 MHz; RF performance at  $V_{DS}$  = 50 V;  $I_{Dq}$  = 20 mA;  $T_{case}$  = 25  $^{\circ}$ C; unless otherwise specified; in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Gp	power gain	P <sub>L</sub> = 110 W	<tbd></tbd>	27	-	dB
RLin	input return loss	P <sub>L</sub> = 110 W	-	<tbd></tbd>	-	dB
$\eta_{D}$	drain efficiency	P <sub>L</sub> = 110 W	<tbd></tbd>	75	-	%

## 7. Test information

### 7.1 Ruggedness in class-AB operation

The BLP05H6110XR is capable of withstanding a load mismatch corresponding to VSWR > 65 : 1 through all phases under the following conditions:  $V_{DS}$  = 50 V;  $I_{Dq}$  = 20 mA;  $P_{L}$  = 110 W pulsed; f = 108 MHz.

## 7.2 Impedance information

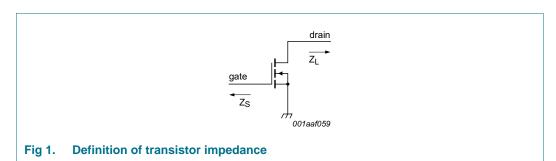


Table 9. Typical push-pull impedance

Simulated  $Z_i$  and  $Z_L$  device impedance; impedance info at  $V_{DS} = 50$  V and  $P_L = 110$  W.

f	Z <sub>i</sub>	Z <sub>L</sub>
(MHz)	(Ω)	(Ω)
108	<tbd></tbd>	<tbd></tbd>

## 7.3 UIS avalanche energy

Table 10. Typical avalanche data per section

 $T_{amb}$  = 25 °C; typical test data; test jig without water cooling.

	•
I <sub>AS</sub>	E <sub>AS</sub>
(A)	(J)
<tbd></tbd>	<tbd></tbd>
<tbd></tbd>	<tbd></tbd>
<tbd></tbd>	<tbd></tbd>

For information see application note AN10273.

## 8. Package outline

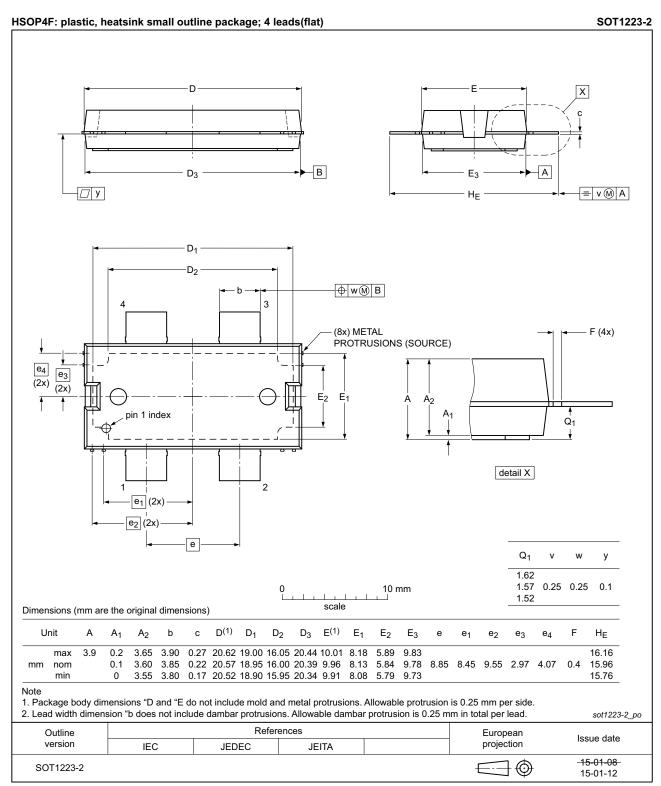


Fig 2. Package outline SOT1223-2 (HSOP4F)

BLP05H6110XR

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## 9. Handling information

#### **CAUTION**



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

## 10. Abbreviations

Table 11. Abbreviations

Acronym	Description
CW	Continuous Wave
ESD	ElectroStatic Discharge
HF	High Frequency
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
MTF	Median Time to Failure
UIS	Unclamped Inductive Switching
VSWR	Voltage Standing-Wave Ratio

## 11. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLP05H6110XR v.1	20150518	Objective data sheet	-	-

## 12. Legal information

#### 12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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#### **Power LDMOS transistor**

## 14. Contents

1	Product profile
1.1	General description 1
1.2	Features and benefits
1.3	Applications
2	Pinning information 2
3	Ordering information
4	Limiting values
5	Thermal characteristics 2
6	Characteristics 3
7	Test information
7.1	Ruggedness in class-AB operation 3
7.2	Impedance information 4
7.3	UIS avalanche energy 4
8	Package outline 5
9	Handling information 6
10	Abbreviations 6
11	Revision history 6
12	Legal information 7
12.1	Data sheet status
12.2	Definitions 7
12.3	Disclaimers
12.4	Trademarks 8
13	Contact information 8
1/	Contents

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